

07-03-00

CPA/28224



CONTINUED PROSECUTION APPLICATION (CPA)
UNDER 37 C.F.R. § 1.53(d)
REQUEST TRANSMITTAL

Address to: Commissioner for Patents Box CPA Washington, D.C. 20231	Attorney Docket No.:	303.229US2
	First Named Inventor:	Leonard Forbes
	Express Mail No.:	EL467292099US
	Total Pages (if by fax):	

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#17
This is a request for filing a continuation application under 37 CFR § 1.53(d) of prior application Serial No. 09/132,157, filed on August 11, 1998, entitled SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH. *Copy for CPA J. McMillan*

The above-identified prior application in which no abandonment of, or termination of, proceedings has occurred, is hereby expressly abandoned as of the filing date of this request for a CPA. Please use all the contents of the prior application file wrapper, including the drawings, as the basic papers for the new application. (37 CFR 1.53(b) must be used for continuation-in-part applications or for applications where the prior application is not to be abandoned.) *7/11/00*

1. Enter the amendment previously filed on under 37 CFR 1.116, but unentered, in the prior application.
2. A Preliminary Amendment (8 pages) is enclosed.
3. This application is filed by fewer than all the inventors named in the prior application, 37 CFR 1.53(d)(4).
 - a. **DELETE** the following inventor(s) named in the prior nonprovisional application:

 - b. The inventor(s) to be deleted are set forth on a separate sheet attached hereto.
4. A new power of attorney is enclosed.
5. Information Disclosure Statement is enclosed.
 - a. Form(s) 1449
 - b. Copies of IDS Citations

07/05/2000 CVORACHA 00000119 09132157

01 FC:131
02 FC:102

690.00 0P
390.00 0P

CONTINUED PROSECUTION APPLICATION (CPA) REQUEST TRANSMITTAL

Page 2 of 2

Inventors: Leonard Forbes
 Prior Application No.: 09/132,157

The filing fee is calculated below on the basis of the claims existing in the prior application as amended at 1 and 2 on the previous page:

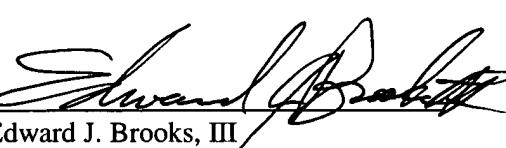
	No. Filed	No. Extra	Rate	Fee
TOTAL CLAIMS	17 - 20 =	0	x 18 =	\$0.00
INDEPENDENT CLAIMS	8 - 3 =	5	x 78 =	\$390.00
[] MULTIPLE DEPENDENT CLAIMS PRESENTED				\$0.00
BASIC FEE				\$690.00
	TOTAL			\$1,080.00

6. Small Entity Status:

- a. A small entity statement is enclosed.
- b. A small entity statement was filed in the prior nonprovisional application and such status is still proper and desired.
- c. Is no longer claimed.

7. A check in the amount of \$1,080.00 is attached to pay the filing fee.8. The Commissioner is hereby authorized to credit overpayments or charge any fees set forth in 37 CFR 1.16 through 1.18 to Deposit Account No. 19-0743.9. A petition for extension of time in the prior application is enclosed along with a check in the amount of \$380.00 to pay the extension fee.10. Other : Declaration of Inventor Under 37 CFR 1.132 (3 pgs.)

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
 P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

By: 
 Atty: Edward J. Brooks, III
 Reg. No. 40,925

Customer Number 21186

"Express Mail" mailing label number EL467292099USDate of Deposit June 30, 2000

I hereby certify that this paper or fee is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 C.F.R. 1.10 on the date indicated above and is addressed to Box CPA, Commissioner for Patents, Washington, D. C. 20231

Shawn L. Hise
 Printed Name

Signature

S/N 09/132,157

JUN 30 2000

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes

Examiner: Mark V. Prenty

Serial No.: 09/132,157

Group Art Unit: 2822

Filed: August 11, 1998

Docket: 303.229US2

Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION
IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed February 2, 2000. Please amend the application as follows:

IN THE CLAIMS

Please cancel claims 12, 29 without prejudice or disclaimer. Please amend claims 11, 24, 25, 28, 30, 38, 40 and 41 as provided below.

11. (Thrice Amended) A p-channel metal-oxide-semiconductor transistor, comprising:
a silicon substrate;
a gate oxide, coupled to the substrate;
a gate, coupled to the gate oxide;
source/drain regions formed in the substrate on opposite sides of the gate; and
a $Si_{1-x}Ge_x$ channel region, having a germanium molar fraction of x, and formed in the substrate, underneath and adjoining the gate oxide and between the source/drain regions;
wherein the $Si_{1-x}Ge_x$ channel region [has a channel length less than $7\mu m$] is formed subsequent to formation of the gate oxide.

24. (Thrice Amended) A p-channel metal-oxide-semiconductor transistor formed on a silicon substrate, comprising:
a $Si_{1-x}Ge_x$ channel region, having a germanium molar fraction of x, and formed in the substrate, underneath and adjoining a gate oxide and between a source region and a drain region;

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